

D, DBQ, DGV, OR PW PACKAGE

(TOP VIEW)

16 🛛 V<sub>CC</sub>

15 🛛 EN

14 S1<sub>D</sub>

13 S2D

12 🛛 D<sub>D</sub>

11 S1<sub>C</sub>

10 S2<sub>C</sub>

9 🛛 D<sub>C</sub>

V<sub>C</sub>C

16

9

2

15 EN

14

13 S2n

12 D<sub>D</sub>

11 S1<sub>C</sub>

10 S2<sub>C</sub>

 $S1_D$ 

INI

2

3

8

z

1

GND

RGY PACKAGE

(TOP VIEW)

S1<sub>A</sub>

S2<sub>A</sub>

D<sub>A</sub> [] 4

S1<sub>B</sub> 🛛 5

S2<sub>B</sub> 🛛 6

D<sub>B</sub> [] 7

GND [

S1<sub>A</sub>

S2<sub>A</sub>

 $D_A$ 

S1<sub>B</sub> 5

S2<sub>B</sub>6

D<sub>B</sub>

2

3

4

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## FEATURES

- Low Differential Gain and Phase (D<sub>G</sub> = 0.82%, D<sub>P</sub> = 0.1 Degree Typ)
- Wide Bandwidth (BW = 300 MHz Min)
- Low Crosstalk (X<sub>TALK</sub> = -80 dB Typ)
- Low Power Consumption (I<sub>CC</sub> = 10 μA Max)
- Bidirectional Data Flow With Near-Zero
   Propagation Delay
- Low ON-State Resistance (r<sub>on</sub> = 3 Ω Typ)
- Rail-to-Rail Switching on Data I/O Ports (0 to V<sub>CC</sub>)
- V<sub>cc</sub> Operating Range From 3 V to 3.6 V
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Data and Control Inputs Provide Undershoot Clamp Diode
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Suitable for Both RGB and Composite-Video Switching

## **DESCRIPTION/ORDERING INFORMATION**

The TS3V330 video switch is a 4-bit 1-of-2 multiplexer/demultiplexer, with a single switch-enable ( $\overline{EN}$ ) input. When  $\overline{EN}$  is low, the switch is enabled and the D port is connected to the S port. When  $\overline{EN}$  is high, the switch is disabled and the high-impedance state exists between the D and S ports. The select (IN) input controls the data path of the multiplexer/demultiplexer.

Low differential gain and phase make this switch ideal for composite and RGB video applications. This device has wide bandwidth and low crosstalk, making it suitable for high-frequency applications as well.

T <sub>A</sub>	PACKA	GE <sup>(1)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	QFN – RGY	Tape and reel	TS3V330RGYR	TF330	
	SOIC – D	Tube	TS3V330D	TC2)/220	
	50IC - D	Tape and reel	TS3V330DR	— TS3V330	
–40°C to 85°C	SSOP (QSOP) – DBQ	Tape and reel	TS3V330DBQR	TF330	
	TOCOD DW	Tube	TS3V330PW	— TF330	
	TSSOP – PW	Tape and reel	TS3V330PWR		
	TVSOP – DGV	Tape and reel	TS3V330DGVR	TF330	

#### **ORDERING INFORMATION**

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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## **DESCRIPTION/ORDERING INFORMATION**

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  feature ensures that damaging current will not backflow through the device when it is powered down. This switch maintains isolation during power off.

To ensure the high-impedance state during power up or power down,  $\overline{EN}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

## **FUNCTION TABLE**

INP	UTS	INPUT/OUTPUT	FUNCTION		
EN	IN	D	FUNCTION		
L	L	S1	D port = S1 port		
L	H S2		D port = S2 port		
н	Х	Z	Disconnect		

#### PIN DESCRIPTION

NAME	DESCRIPTION
S1, S2	Analog video I/Os
D	Analog video I/Os
IN	Select input
EN	Switch-enable input

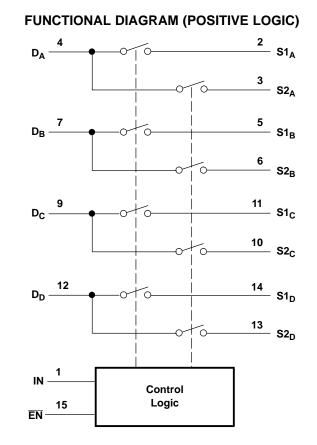
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## PARAMETER DEFINITIONS

PARAMETER	DESCRIPTION
R <sub>on</sub>	Resistance between the D and S ports, with the switch in the ON state
I <sub>OZ</sub>	Output leakage current measured at the D and S ports, with the switch in the OFF state
I <sub>OS</sub>	Short-circuit current measured at the I/O pins
V <sub>IN</sub>	Voltage at IN
V <sub>EN</sub>	Voltage at EN
C <sub>IN</sub>	Capacitance at the control (EN, IN) inputs
C <sub>OFF</sub>	Capacitance at the analog I/O port when the switch is OFF
C <sub>ON</sub>	Capacitance at the analog I/O port when the switch is ON
V <sub>IH</sub>	Minimum input voltage for logic high for the control (EN, IN) inputs
V <sub>IL</sub>	Minimum input voltage for logic low for the control (EN, IN) inputs
V <sub>H</sub>	Hysteresis voltage at the control (EN, IN) inputs
V <sub>IK</sub>	I/O and control (EN, IN) inputs diode clamp voltage
VI	Voltage applied to the D or S pins when D or S is the switch input
Vo	Voltage applied to the D or S pins when D or S is the switch output
I <sub>IH</sub>	Input high leakage current of the control (EN, IN) inputs
Ι <sub>ΙL</sub>	Input low leakage current of the control (EN, IN) inputs
l <sub>l</sub>	Current into the D or S pins when D or S is the switch input
Ι <sub>Ο</sub>	Current into the D or S pins when D or S is the switch output
l <sub>off</sub>	Output leakage current measured at the D or S ports, with $V_{CC} = 0$
t <sub>ON</sub>	Propagation delay measured between 50% of the digital input to 90% of the analog output when switch is turned ON
t <sub>OFF</sub>	Propagation delay measured between 50% of the digital input to 90% of the analog output when switch is turned OFF
BW	Frequency response of the switch in the ON state measured at -3 dB
X <sub>TALK</sub>	Unwanted signal coupled from channel to channel. Measured in $-dB$ . $X_{TALK} = 20 \log V_O/V_I$ . This is a nonadjacent crosstalk.
O <sub>IRR</sub>	Off isolation is the resistance (measured in –dB) between the input and output with the switch OFF.
D <sub>G</sub>	Magnitude variation between analog input and output pins when the switch is ON and the dc offset of composite-video signal varies at the analog input pin. In the NTSC standard, the frequency of the video signal is 3.58 MHz, and dc offset is from 0 to 0.714 V.
D <sub>P</sub>	Phase variation between analog input and output pins when the switch is ON and the dc offset of composite-video signal varies at the analog input pin. In the NTSC standard, the frequency of the video signal is 3.58 MHz, and dc offset is from 0 to 0.714 V.
I <sub>CC</sub>	Static power-supply current
I <sub>CCD</sub>	Variation of I <sub>CC</sub> for a change in frequency in the control (EN, IN) inputs
$\Delta I_{CC}$	This is the increase in supply current for each control input that is at the specified voltage level, rather than V <sub>CC</sub> or GND.

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## Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	4.6	V
V <sub>IN</sub>	Control input voltage range <sup>(2)(3)</sup>		-0.5	4.6	V
V <sub>I/O</sub>	Switch I/O voltage range <sup>(2)(3)(4)</sup>		-0.5	4.6	V
I <sub>IK</sub>	Control input clamp current	V <sub>IN</sub> < 0		-50	mA
I <sub>I/OK</sub>	I/O port clamp current	V <sub>I/O</sub> < 0		-50	mA
I <sub>I/O</sub>	ON-state switch current <sup>(5)</sup>			±128	mA
	Continuous current through $V_{CC}$ or GND			±100	mA
		D package <sup>(6)</sup>		73	
		DBQ package <sup>(6)</sup>		90	
$\theta_{JA}$	Package thermal impedance	DGV package		120	C/W
		PW package <sup>(6)</sup>		108	
		RGY package <sup>(7)</sup>		39	
T <sub>stg</sub>	Storage temperature range	· · · ·	-65	150	С

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- All voltages are with respect to ground, unless otherwise specified. (2)
- The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed. (3)

(4)

 $V_I$  and  $V_O$  are used to denote specific conditions for  $V_{I/O}$ .  $I_I$  and  $I_O$  are used to denote specific conditions for  $I_{I/O}$ . (5)

The package thermal impedance is calculated in accordance with JESD 51-7. (6)

The package thermal impedance is calculated in accordance with JESD 51-5. (7)

## Recommended Operating Conditions<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	3	3.6	V
V <sub>IH</sub>	High-level control input voltage (EN, IN)	2	$V_{CC}$	V
V <sub>IL</sub>	Low-level control input voltage (EN, IN)	0	0.8	V
V <sub>ANALOG</sub>	Analog I/O voltage	0	$V_{CC}$	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, (1) Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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### **Electrical Characteristics**

over recommended operating free-air temperature range, V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V (unless otherwise noted)

PARAMETER			TEST CONDITI	ONS <sup>(1)</sup>		MIN TYP <sup>(2)</sup>	MAX	UNIT
V <sub>IK</sub>	EN, IN	V <sub>CC</sub> = 3 V,	I <sub>IN</sub> = -18 mA				-1.8	V
V <sub>hys</sub>	EN, IN					150		mV
I <sub>IH</sub>	EN, IN	V <sub>CC</sub> = 3.6 V,	$V_{IN}$ and $V_{EN} = V_{CC}$				±1	μA
IIL	EN, IN	V <sub>CC</sub> = 3.6 V,	$V_{IN}$ and $V_{EN} = GND$				±1	μA
$I_{OZ}^{(3)}$		V <sub>CC</sub> = 3.6 V,	$V_0 = 0$ to 3.6 V,	$V_{I} = 0,$	Switch OFF		±1	μA
$I_{OS}^{(4)}$		V <sub>CC</sub> = 3.6 V,	$V_{O} = 0.5 V_{CC,}$	$V_{I} = 0,$	Switch ON	50		mA
I <sub>off</sub>		$V_{CC} = 0 V,$	$V_0 = 0$ to 3.6 V,	$V_I = 0$			15	μA
I <sub>CC</sub>		V <sub>CC</sub> = 3.6 V,	$I_{I/O} = 0,$	Switch ON or 0	OFF		10	μA
$\Delta I_{CC}$	EN, IN	V <sub>CC</sub> = 3.6 V,	One input at 3.4 V,	Other inputs at	t V <sub>CC</sub> or GND		750	μA
		V <sub>CC</sub> = 3.6 V,	$V_{EN} = GND$	V <sub>EN</sub> = GND D and S ports open,				mA/
ICCD		VIN input switching 8	50% duty cycle				0.45	MHz
CIN	EN, IN	$V_{IN}$ of $V_{EN} = 0$ ,	f = 1 MHz			3.5		pF
<u> </u>	D port	V O	£ 1 MIL-			10		~ <b>C</b>
C <sub>OFF</sub>	S port	$-V_{I} = 0,$	f = 1 MHz,	Outputs open,	Switch OFF	5		pF
C <sub>ON</sub>		V <sub>1</sub> = 0,	f = 1 MHz,	Outputs open,	Switch ON	17		pF
<b>r</b> (5)		V 2.V	V <sub>I</sub> = 1 V,	I <sub>O</sub> = 13 mA,	$R_L$ = 75 $\Omega$	5	7	0
r <sub>on</sub> <sup>(5)</sup>		$V_{CC} = 3 V$	V <sub>I</sub> = 2 V,	I <sub>O</sub> = 26 mA,	$R_L$ = 75 $\Omega$	7	10	Ω

(1) V<sub>I</sub>, V<sub>O</sub>, I<sub>I</sub>, and I<sub>O</sub> refer to I/O pins. (2) All typical values are at V<sub>CC</sub> = 5 V (unless otherwise noted), T<sub>A</sub> = 25°C.

(3) For I/O ports, I<sub>OZ</sub> includes the input leakage current.
(4) The I<sub>OS</sub> test is applicable to only one ON channel at a time. The duration of this test is less than one second.
(5) Measured by the voltage drop between the D and S terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (D or S) terminals.

## **Switching Characteristics**

over recommended operating free-air temperature range, V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V, R<sub>L</sub> = 75  $\Omega$ , C<sub>L</sub> = 20 pF (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	ΜΙΝ ΤΥ	P MAX	UNIT
t <sub>ON</sub>	S	D	2	.5 6.5	ns
t <sub>OFF</sub>	S	D	1	.1 3.5	ns

## **Dynamic Characteristics**

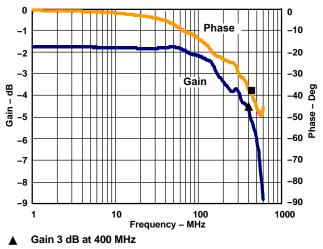
over recommended operating free-air temperature range, V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V (unless otherwise noted)

PARAMETER		TYP <sup>(1)</sup>	UNIT		
D <sub>G</sub> <sup>(2)</sup>	$R_L = 150 \Omega$ ,	f = 3.58 MHz,	See Figure 6	0.82	%
D <sub>P</sub> <sup>(2)</sup>	R <sub>L</sub> = 150 Ω,	f = 3.58 MHz,	See Figure 6	0.1	Deg
BW	$R_L = 150 \Omega$ ,	See Figure 7		300	MHz
X <sub>TALK</sub>	$R_L = 150 \ \Omega,$	f = 10 MHz,	RIN = 10 $\Omega$ , See Figure 8	-80	dB
O <sub>IRR</sub>	$R_L = 150 \Omega$ ,	f = 10 MHz,	See Figure 9	-50	dB

(1) All typical values are at  $V_{CC} = 5 V$  (unless otherwise noted),  $T_A = 25^{\circ}C$ . (2)  $D_G$  and  $D_P$  are expressed in absolute magnitude.

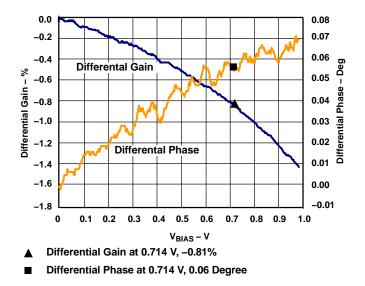
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## **TYPICAL CHARACTERISTICS**



■ Phase at 3-dB Frequency, –38.28 Degrees

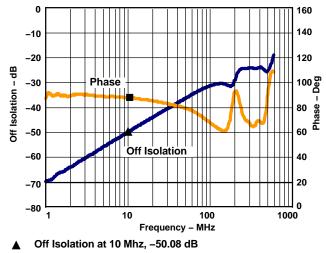
Figure 1. Gain/Phase vs Frequency





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■ Phase at 10 MHz, 87.8 Degrees

Figure 3. Off Isolation vs Frequency

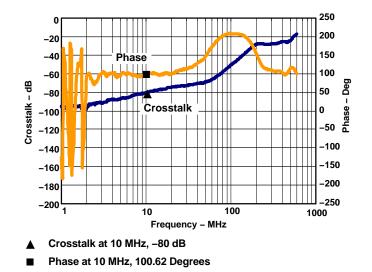
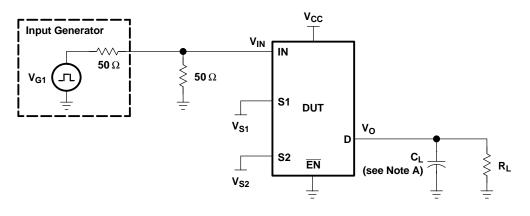


Figure 4. Crosstalk vs Frequency



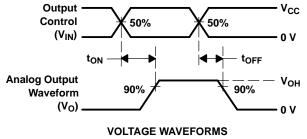
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## PARAMETER MEASUREMENT INFORMATION



TEST	V <sub>CC</sub>	RL	CL	V <sub>S1</sub>	V <sub>S2</sub>
t <sub>ON</sub>	3.3 V $\pm$ 0.3 V 3.3 V $\pm$ 0.3 V	75 75	20 20	GND V <sub>CC</sub>	V <sub>CC</sub> GND
t <sub>OFF</sub>	3.3 V $\pm$ 0.3 V 3.3 V $\pm$ 0.3 V	75 75	20 20	GND V <sub>CC</sub>	V <sub>CC</sub> GND

#### **TEST CIRCUIT**



ton AND toFF TIMES

NOTES: A.  $C_L$  includes probe and jig capacitance.

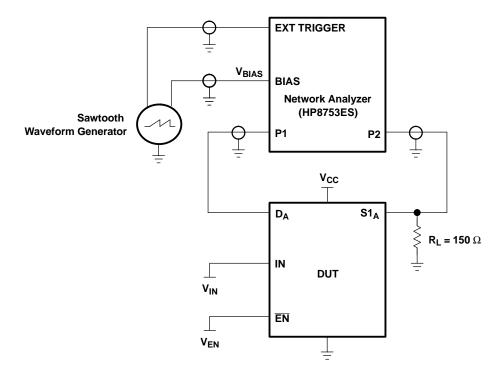
- B. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>0</sub> = 50  $\Omega$ , t<sub>r</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.
- C. The outputs are measured one at a time, with one transition per measurement.

Figure 5. Test Circuit and Voltage Waveforms

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#### PARAMETER MEASUREMENT INFORMATION



NOTE: For additional information on measurement method, refer to the TI application report, *Measuring Differential Gain and Phase*, literature number SLOA040.

#### Figure 6. Test Circuit for Differential Gain/Phase Measurement

Differential gain and phase are measured at the output of the ON channel. For example, when  $V_{IN} = 0$ ,  $V_{EN} = 0$ , and  $D_A$  is the input, the output is measured at S1<sub>A</sub>.

### HP8753ES Setup

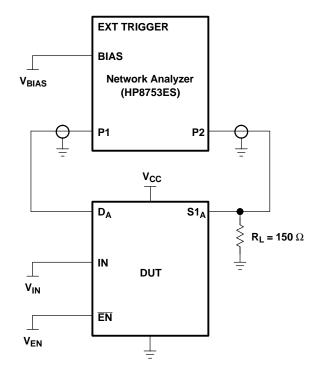
Average = 20 RBW = 300 Hz ST = 1.381 s P1 = -7 dBM CW frequency = 3.58 MHz

#### Sawtooth Waveform Generator Setup

 $V_{BIAS} = 0$  to 1 V Frequency = 0.905 Hz

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## PARAMETER MEASUREMENT INFORMATION





Frequency response is measured at the output of the ON channel. For example, when  $V_{IN} = 0$ ,  $V_{EN} = 0$ , and  $D_A$  is the input, the output is measured at S1<sub>A</sub>. All unused analog I/O ports are left open.

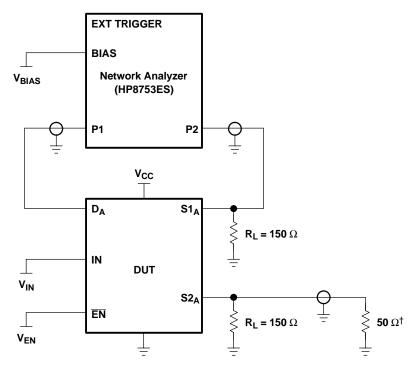
## HP8753ES Setup

 $\begin{array}{l} \text{Average} = 4 \\ \text{RBW} = 3 \text{ kHz} \\ \text{V}_{\text{BIAS}} = 0.35 \text{ V} \\ \text{ST} = 2 \text{ s} \\ \text{P1} = 0 \text{ dBM} \end{array}$ 

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## PARAMETER MEASUREMENT INFORMATION



 $^\dagger$  A 50- $\!\Omega$  termination resistor is needed for the Network Analyzer.

#### Figure 8. Test Circuit for Crosstalk (X<sub>TALK</sub>)

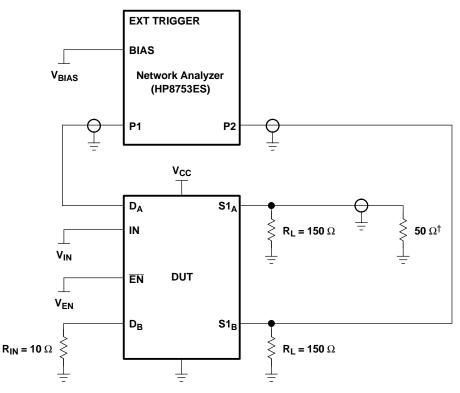
Crosstalk is measured at the output of the nonadjacent ON channel. For example, when  $V_{IN} = 0$ ,  $V_{EN} = 0$ , and  $D_A$  is the input, the output is measured at S1<sub>B</sub>. All unused analog input (D) ports and output (S) ports are connected to GND through 10- $\Omega$  and 50- $\Omega$  pulldown resistors, respectively.

#### HP8753ES Setup

Average = 4 RBW = 3 kHz  $V_{BIAS}$  = 0.35 V ST = 2 s P1 = 0 dBM

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## PARAMETER MEASUREMENT INFORMATION



<sup>†</sup> A 50- $\Omega$  termination resistor is needed for the network analyzer.

#### Figure 9. Test Circuit for Off Isolation (OIRR)

Off isolation is measured at the output of the OFF channel. For example, when  $V_{IN} = V_{CC}$ ,  $V_{EN} = 0$ , and  $D_A$  is the input, the output is measured at S1<sub>A</sub>. All unused analog input (D) ports are left open, and output (S) ports are connected to GND through 50- $\Omega$  pulldown resistors.

#### HP8753ES Setup

Average = 4 RBW = 3 kHz  $V_{BIAS}$  = 0.35 V ST = 2 s P1 = 0 dBM



11-Apr-2013

# PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings (4)	Samples
TS3V330D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330DBQR	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF330	Samples
TS3V330DBQRE4	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF330	Samples
TS3V330DBQRG4	ACTIVE	SSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF330	Samples
TS3V330DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330DGVR	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330DGVRE4	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330DGVRG4	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V330	Samples
TS3V330PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330PWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples
TS3V330PWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF330	Samples



11-Apr-2013

Orderable Device		Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish		Op Temp (°C)	Top-Side Markings	Samples
TS3V330PWRG4	(1) ACTIVE	TSSOP	PW	16	2000	(2) Green (RoHS & no Sb/Br)	CU NIPDAU	(3) Level-1-260C-UNLIM	-40 to 85	(4) TF330	Samples
TS3V330RGYR	ACTIVE	VQFN	RGY	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF330	Samples
TS3V330RGYRG4	ACTIVE	VQFN	RGY	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF330	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE AND REEL INFORMATION

#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3V330DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
TS3V330DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TS3V330PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TS3V330RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

14-Jul-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3V330DGVR	TVSOP	DGV	16	2000	367.0	367.0	35.0
TS3V330DR	SOIC	D	16	2500	333.2	345.9	28.6
TS3V330PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TS3V330RGYR	VQFN	RGY	16	3000	367.0	367.0	35.0

# **MECHANICAL DATA**

PLASTIC SMALL-OUTLINE

MPDS006C - FEBRUARY 1996 - REVISED AUGUST 2000

## DGV (R-PDSO-G\*\*)

24 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153

14/16/20/56 Pins – MO-194



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



PW (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.  $\beta$ . This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153



# PW (R-PDSO-G16)

# PLASTIC SMALL OUTLINE



- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# **MECHANICAL DATA**



- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Æ Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated.
- The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



# RGY (R-PVQFN-N16)

# PLASTIC QUAD FLATPACK NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



#### NOTE: All linear dimensions are in millimeters





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



DBQ (R-PDSO-G16)

PLASTIC SMALL-OUTLINE PACKAGE



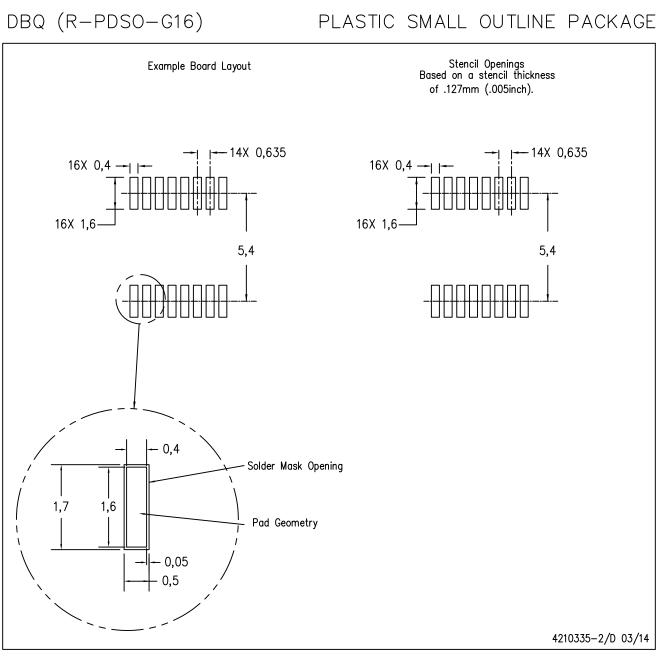
NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.

D. Falls within JEDEC MO-137 variation AB.





NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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